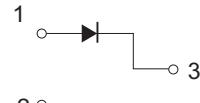




迈拓电子
MAITUO ELECTRONIC

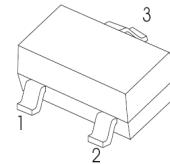
1SS193 Switching Diode



FEATURES

- Low forward voltage
- Fast reverse recovery time

MARKING: F3



SOT-23

Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V _{RM}	85	V
DC Blocking Voltage	V _R	80	V
Forward Continuous Current	I _{FM}	300	mA
Average Rectified Output Current	I _O	100	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I _{FSM}	2.0	A
Power Dissipation	P _D	150	mW
Thermal Resistance from Junction to Ambient	R _{θJA}	833	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55~+150	°C

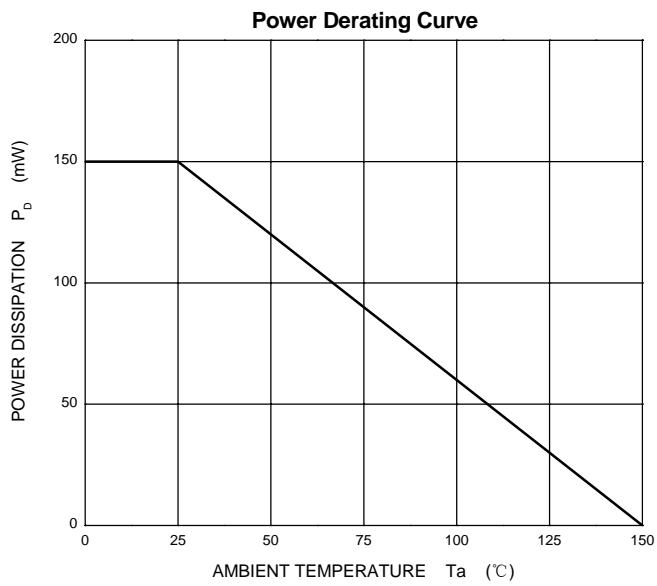
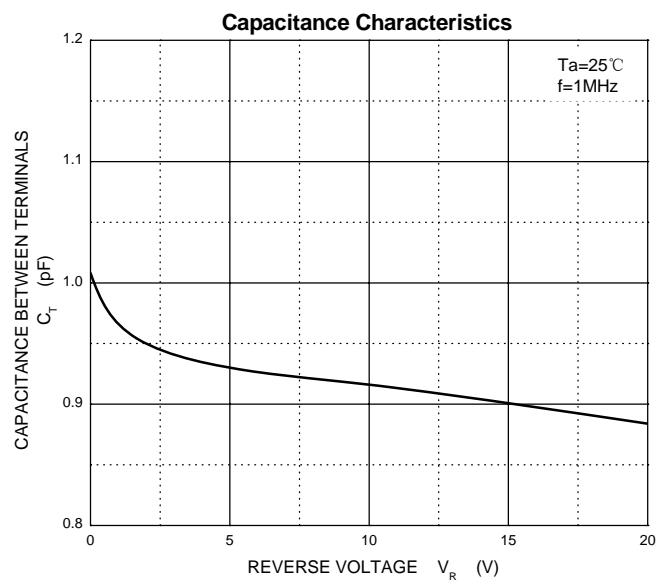
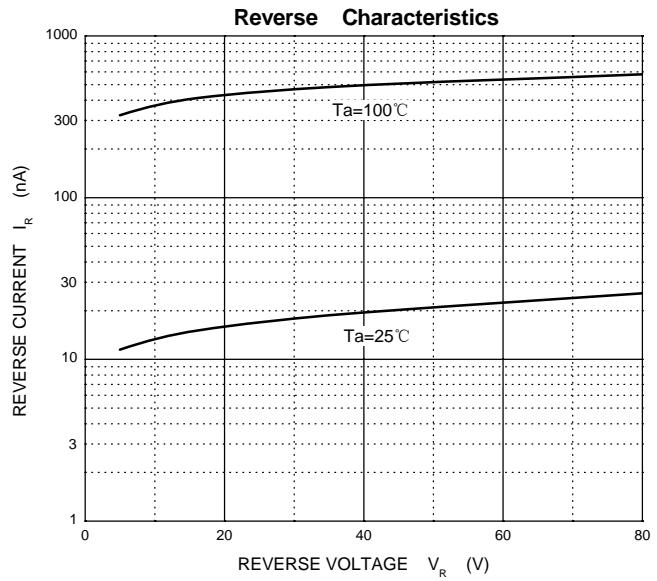
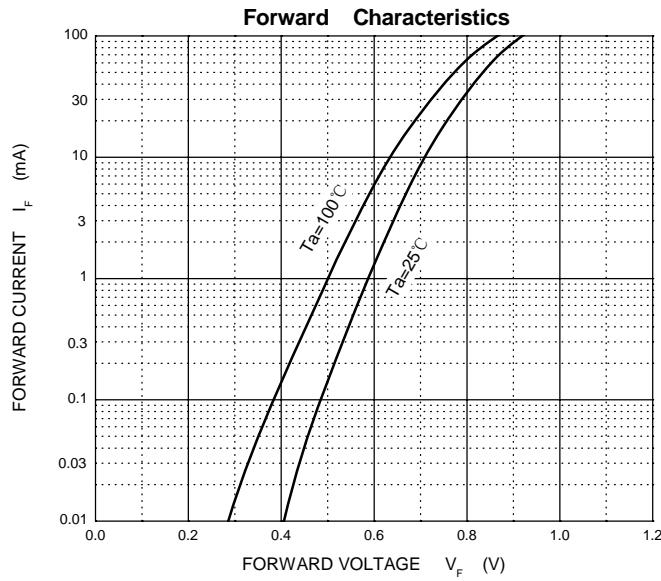
Electrical Characteristics @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V _(BR)	80			V	I _R =100μA
Forward voltage	V _{F1}		0.60		V	I _F =1mA
	V _{F2}		0.72		V	I _F =10mA
	V _{F3}		0.90	1.2	V	I _F =100mA
Reverse current	I _{R1}			0.1	uA	V _R =30V
	I _{R2}			0.5	uA	V _R =80V
Capacitance between terminals	C _T		0.9	3.0	pF	V _R =0,f=1MHz
Reverse recovery time	t _{rr}		1.6	4.0	ns	I _F =I _R =10mA,I _{rr} =0.1×I _R



迈拓电子
MAITUO ELECTRONIC

Typical Characteristics



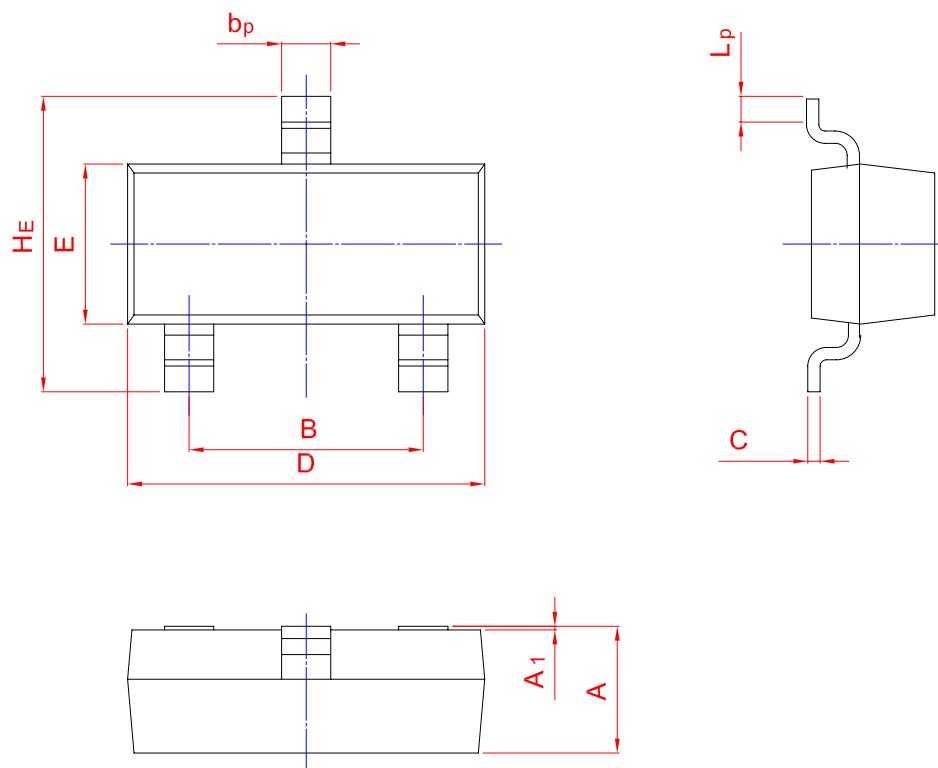


迈拓电子
MAITUO ELECTRONIC

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20